# LED970-06 infrared LED

On forward bias it emits a spectral band of radiation, which peaks at 970nm.

### Specifications

1) Product Name Infrared LED Lamp 1 970-08

### 2) Type No.

3) Chip (1) Chip Material GaAs

(2) Peak Wavelength 970nm tvp. 4) Package

## (1) Type

Φ5mm clear molding

(2) Resin Material Epoxy Resin Soldered (3) Lead Frame

		5 mox. 21mis.
63.5110.2	8.7±0.2	Cothode
$\bigcirc$	3-0:	begin Anode

+Outer dimension (Unit: mm)

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature Ta=25°C	
Power Dissipation	Po	140	mW		
Forward Current	lF	100	mA	Ta=25°C	
Pulse Forward Current	IFP	1000	mA	Ta=25°C	
Reverse Voltage	VR	5	V	Ta=25°C	
Operating Temperature	TOPR	-30 ~ +85	°C		
Storage Temperature	Tstg	-30 ~ +100	°C		
Soldering Temperature	TsoL	260	°C		

±Pulse Forward Current condition; Dutv=1% and Pulse Width=10us.

±Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

# - Electro Ontical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	Ir=50mA	2000	1.30	1.45	V
Reverse Current	IR	VR=5V			10	uA
Total Radiated Power	Po	Ir=50mA	2.5	4.0	T	mW
Radiant Intensity	lv	Ir=50mA		20		mW/sr
Peak Wavelength	λο	Ir=50mA	960	970	980	nm
Half Width	Δλ.	Ir=50mA		65	T	nm
Viewing Half Angle	θ 1/2	Ir=50mA		±7		deg.
Rise Time	tr	Ir=50mA		1000	T	ns
Fall Time	tf	Ir=50mA		400	1	ns

‡Total Radiated Power is measured by Photodyne #500 ‡Radiant Intensity is measured by Tektronix J-6512